

The Study of Manufacturing Methodology of Nanocrystals in Science and Engineering

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Abstract

Chemical vapor transport (CVT) is known as one of the most efficient methods of synthesizing nanocrystals. In order to investigate the underlying phenomena in CVT processes, especially the growth rate and growth quality in relation to total pressure, temperatures of source and crystal ends, as well as the entangled chemical reactions, CFD modeling is pursued as a powerful and effective tool in lieu of expensive experimental work. CFD modeling has become an important component of the research or a new research methodology and will become increasingly important for simplifying the investigation of phenomena in processes. This paper is presented on how CFD modeling approach can be used as a research methodology in sciences and engineering. Two-dimensional numerical modeling on closed ampoule chemical vapor transport of ZnS-I₂ system is conducted. The transport rate (TR) and its transition from diffusion-dominated to convection-dominated regimes in relation to total pressure, average temperature is studied intensively. Modeling results reveal that, the transition of TR from diffusion-dominated to convection-dominated regimes depends on P. Compared to the experimental literature values for all growth regimes, the modeling results agree with the experimental data.

Keywords: Research methodology; CFD Modeling; Chemical Vapor Transport; Transport Phenomena

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1. Introduction

Chemical vapor transport (CVT) processes constitute an important technology for manufacturing nanocrystals [1]. The production rate or growth of nanocrystals in a CVT ampoule depends on process conditions such as temperature, pressure, reaction kinetic and reactant concentrations. These process conditions can vary throughout the CVT ampoule. The tremendous increase in complexity of nanocrystals products leads to a continuous need for new CVT process and equipment, fulfilling ever increasing performance demands [2]. This performance is determined by the interacting influences of hydrodynamics and chemical kinetics in a CVT

ampoule, which in turn depend on the process conditions. As a result of this complexity, experimental studies with trial and error methods have always played an important role in CVT process and equipment development. However, the need for a more systematic approach or a new research methodology has been recognized, and has led to the development and application of process models of increasing complexity [2]. Modeling of these systems will provide important aids to the scientific understanding and engineering scale-up of these devices. In particular, CFD modeling should be helpful in interpreting nanocrystal growth rates, transport rates and reaction temperature. Such a CFD

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modeling is the topic of this paper. We present modeling results for the two-dimensional velocity, temperature and transport rate profiles in a two-dimensional CVT ampoule. The geometry is simple, allowing for the easy production of the results, and focused on the CFD modeling as a new research methodology. The chemistry model used is that by Zuo and Wang, which has been extensively documented and tested [3, 4].

2. Literature review

Although many experimental studies on transport phenomena in closed ampoules have appeared in the literature, most of them are for physical vapor transport (PVT) [5-6], there are few modeling studies on CVT [3,4]. Although the modeling results on PVT provide a good reference frame, they cannot simply be applied, without differentiation, to CVT processes for the following reasons. (1) Unlike PVT, carrier gas in CVT is no longer inert but will react with source and crystal surfaces, thus both mass flux and mass concentration on the two surfaces are much different from that derived in PVT. (2) In PVT with the carrier gas present, system pressure usually varies slightly around 0.05 atm and temperature difference between the two ends is usually less than 10K, which often results in either diffusion-dominated or convection dominated transport modes. While in CVT, pressure is usually in the order of 1 atm, temperature difference varies from as small as 3K to as large as 500K, but mostly around 10–100K. For these reasons flow patterns and transport modes in CVT are different from that

in PVT. (3) Because of the small temperature and pressure variations in PVT, the compressibility effect is usually neglected and thermo-physical parameters can be assumed constant. While in CVT, due to large differences in temperature and pressure that usually occur, the compressibility effect and variations of thermo physical parameters with temperature and pressure can no longer be ignored and have to be considered. Comparisons between PVT and CVT in relation to transport phenomena are listed in table 1.

For modeling of an enclosure filled with vapor with differentially heated end walls (Figure 1), there are mainly four approaches to build the velocity boundary condition at the source and crystal surfaces. The first is to totally ignore the effect of interfacial mass transport that corresponds to the case of pure thermal convection induced by the differentially heated end walls (the effect of concentration gradient being neglected). This is the case that has been studied by Klosse and Ullersma. The second is to impose a fixed velocity at the interface as done by Extremet et al. [7]. It involves an arbitrarily chosen proportional factor and, in general, is not easily used. The third is to relate the interfacial velocity to the concentration gradient by considering species conservation at the interface with inert carrier gas condition, which was derived by Rosenberger et al. [8] and has been widely used for PVT processes [5, 6]. The fourth is a non-equilibrium, surface kinetics-related boundary condition, which was derived by Zappoli et al. [9] and was used in a two-dimensional rectangular model of the GeI2/GeI4 CVT system.

Table 1. Comparisons between PVT and CVT in relation to transport phenomena [4].

Parameters	Physical vapor transport (PVT)	Chemical vapor transport (CVT)
Growth mechanism	Monatomic, associative	Reversible chemical reactions
Carrier gas	Inert	Reacting
Growth temperature (T)	Sublimation point (typical 1000 K)	Typical 100K less than sublimation point
Temperature difference	1–10 K	3–500K
Total system pressure	High vacuum or inert gas	1–3atm
Thermo physical parameters	Constant	Varying
Compressibility effect	Insignificant	Significant
Aspect ratio (L/d)	Typical 5	Typical 10
Possible flow pattern	Diffusion, advection mass convection	Diffusion, advection and thermal convection

However, because of the complicated surface kinetics involved, the boundary condition of this model is hard to apply to the general CVT process at chemical equilibrium conditions. It is the purpose of this paper to explore the underlying phenomena in the kinetic process of closed ampoule CVT, especially the relationship between the bulk diffusion/advection. In doing so, we try to develop

a general expression for the mass transport rate and a widely accepted velocity boundary condition at the vapor/solid interface.

In the study, we concentrate on the kinetic process of the ZnS–I2 system, because this system has been most widely studied and has the most data available. Specifically, under the condition of equilibrium chemical reactions, partial pressures

of various species near the source and crystal surfaces will be determined. By considering species conservation at the solid/vapor interface in relation to stoichiometric chemical reactions, the expressions of transport rate and mass average velocity in the vapor/solid interface will be established and will later be used in solving coupled conservation equations for the general two-dimensional CVT process. Furthermore, we present experimental validations of the model with published data.

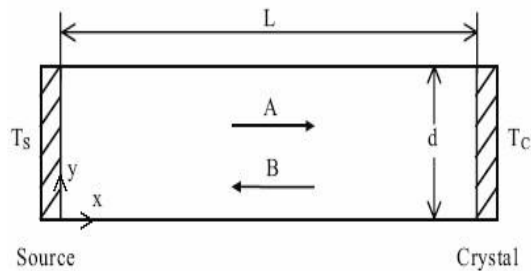
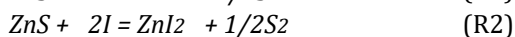
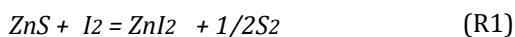


Figure 1. Schematic and coordinates of closed ampoule

3. Chemical reactions and partial pressures

Due to chemical reactions occurring at the source and crystal ends in the CVT ampoule, species in the vapor mixture are either created or destroyed in the vapor/solid interface (assuming the gas phase reaction to be neglected). Thus, partial pressures in the ampoule are affected strongly by heterogeneous chemical reactions. In order to construct a physical model for mass transport, we need to consider the specific chemical reactions in equilibrium at the source and crystal surfaces so as to determine the species partial pressures and consequently the velocity and mass transport rate expressions for the CVT system. In CVT process, diatomic iodine I_2 is widely used as a carrier gas (transport agent). We consider the $ZnS-I_2$ system at temperatures between 1000 and 1100 K, which covers the actual crystal growth temperature range from previous experimental practices. In this temperature range, the following species exist in significant amount in the vapor phase: I_2 , I , ZnI_2 and S_2 , other gas species such as ZnI , Zn and S are tiny and can be neglected. Thus, we consider the following reactions occurring simultaneously in the system:



In the above reactions, reaction (R2) can be obtained by subtracting reaction (R3) from (R1), thus, only reactions (R1) and (R3) are independent and need be considered. Based on the above reactions, the partial pressure of each species can be determined by the following equilibrium equations:

$$K_1 = P_{ZnI_2} (0.5 P_{ZnI_2})^{0.5} / P_{I_2} \quad (1)$$

$$K_3 = (P_I)^2 / P_{I_2} \quad (2)$$

$$P_{I_2} + P_I + 1.5 P_{ZnI_2} = P \quad (3)$$

In the above, the ideal gas behavior for all gas species is assumed. The stoichiometric relation $P_{S_2} = 0.5 P_{ZnI_2}$ has been used in Eqs. (1) and (3). Eq. (3) is derived from the molar conservation of total species. Total system pressure, P , is assumed constant everywhere, which implies that a temperature difference in the ampoule will mainly cause a density difference—the driving force of thermal convection, but not a pressure difference, since pressure can propagate quickly through an enclosure and even up the non-uniformities, according to the theory of fluid mechanics. The equilibrium constant, K_i , for reaction i ($i = 1, 2, 3$) as a function of temperature, T , can be determined by using the Arrhenius equation. The thermo chemical parameters used in our derivation are taken from Ref. [4].

4. CFD model

4.1. Ampoule model

We adopt a horizontal rectangular enclosure with two vertical end walls (source and crystal ends) fixed at different temperatures as our physical model (Figure 1). The width of the enclosure is assumed much larger than the height. In this way, we can ignore the dimension of width and use a two dimensional rectangular model to simulate the vertical mid-plane of a real three-dimensional cylindrical ampoule. Consider the enclosure filled with a vapor mixture consisting of mainly four species: I_2 , I , ZnI_2 and S_2 .

4.2. Transport model

To find the transport rate of ZnI_2 particles and the influencing parameters, we need to solve the coupled conservation equations of mass, momentum, species and energy in steady state. Since there exists a rather high temperature (1000–1100 K) and temperature difference (100 K) in the common CVT system, density change is significant and Boussinesq approximation is no longer valid. In order to minimize the modeling errors, general conservation equations including the compressibility effect and the varying thermo physical parameters with temperature and pressure are adopted. According to Patankar [10], the four partial differential equations from the conservation laws can be represented by the generic equation:

$$\Delta \cdot (\rho u \phi) = \Delta \cdot (\Gamma \Delta \phi) + S \quad (4)$$

Where $\Delta = \partial / \partial x + \partial / \partial y$, ϕ represents the corresponding variable in each conservation

equation, and all other terms are assumed constant during each numerical interpolation step. The terms in equation (4) for different conservation equations are listed in table 2. Since I_2 particles are no longer inert, but penetrate into or out of the source or crystal surface and react with the surface,

$$\text{Source end} \quad u(0, y) = f(\partial w / \partial x), v(0, y) = 0, T(0, y) = T_s, w(0, y) = f(M_i, P) \quad (5)$$

$$\text{Crystal end} \quad u(L, y) = f(\partial w / \partial x), v(L, y) = 0, T(L, y) = T_c, w(L, y) = f(M_i, P) \quad (6)$$

$$\text{Walls} \quad u(0, y) = u(L, y) = 0, v(0, y) = v(L, y) = 0, T(0, y) = T(L, y) = T_s - (T_s - T_c)x/L, w(0, y) = w(L, y) = ws - (ws - wc)x/L \quad (7)$$

Conservation equations in the form of equation (4) with boundary conditions equations (5) – (7) are solved with a finite volume computer code SIMPLE [10]. The grid mesh is 50 * 100. The program is run on a PVI PC. In each calculation, depending upon the total pressure parameter, it takes about 1500–2500 iterations to reach convergence.

4.3. Gas properties

The above model equations comprise thermo-chemical (specific heat, heat of formation and

both velocity and mass component boundary conditions are different from that in PVT. The boundary conditions for velocity, temperature and mass components can be expressed as follows (w denoting w_A for convenience),

entropy) and transport (viscosity, thermal conductivity and diffusivities) properties of the gas mixture in the ampoule. Thermochemical properties of gases can be found in e.g.[3, 4]. Here, we have used the thermo-chemical properties as a function of temperature. The transport equations and the calculation of thermo-chemical and transport properties apply generally to multicomponent gas mixtures at moderate temperature and pressure.

Table 2. Variables and constants corresponding to Eq. (4) in different conservation equations

	ϕ	Γ	S
Mass conservation	1	0	0
x-momentum conservation	u	μ	$\partial \rho / \partial x$
y-momentum conservation	v	μ	$\partial \rho / \partial y - \rho g_y$
Energy conservation	T	k/c	0
Mass component conservation	w	ρD	$\partial w / \partial x$

5. Modeling results and discussions

5.1. Transport rate as function of total system pressure

The variation of transport rate (TR) with system pressure (P) is depicted in figure 2. This figure also gives the comparison between the modeling results and the experimental ones from the literature. The TR are calculated and averaged over the whole crystal surface (over y-direction). The continuous curves are drawn from discrete calculations of TR at each individual pressure at selected ampoule geometry and temperature. The calculated transport rates in figure 2 are compared with the experimental ones from Dangel and Wuensch [11] for the same growth conditions. Figure 2 shows that the predicted values agree qualitatively with the experimental ones for entire pressure range. Although the predicted TR values are approximate, give good predictions for the transition points from the diffusion-dominated to convection-dominated regimes.

5.2. Flow pattern, flow transition and flux transition

From numerical modeling results, we find that the transition of transport rate is different from the

transition of flow pattern. To distinguish the two different transitions, we call the former the flux transition and the latter the flow transition.

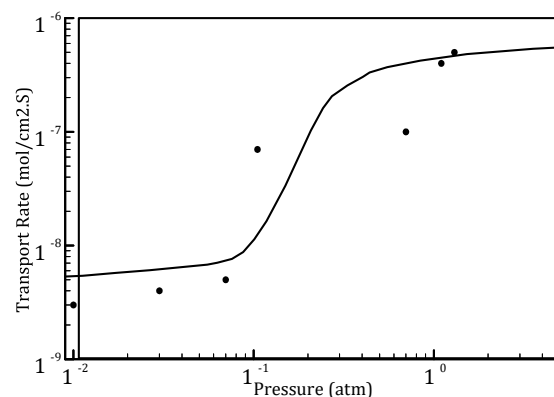


Figure 2. Transport rate as a function of total pressure, discrete points are the experimental data [4].

Figures 3-5 show the changes of flow patterns from pure diffusion/advection ($P = 0.01$ atm) to flow transition ($P = 0.03$ atm) and to full circulatory convection ($P = 0.1$ atm) for $d = 1.5$ cm, $L = 14$ cm, $T_s = 1063K$ and $T_c = 1013K$ condition. Comparing to figure 2, we find that at the same growth condition, the flow transition occurs at much lower pressure

($P=0.03$ atm) than the flux transition ($P=0.4$ atm), i.e., the flow may be in circulatory convection while the transport may still be dominated by the diffusion/advection mode. By determining the onset pressure for flow transition at different growth conditions (Figure 2), it is estimated that the pressure for flow transition is about $1/13$ of that for flux transition under the same temperature and geometric conditions. To extend this result, more numerical calculations for higher temperature differences are needed.

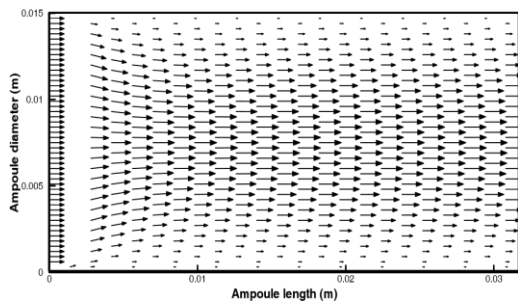


Figure 3. Flow patterns for pure diffusion.

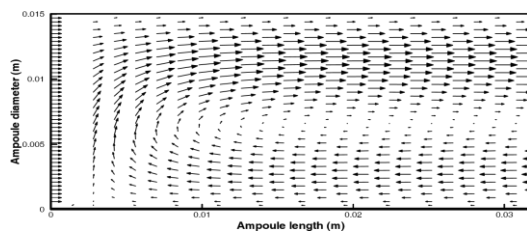


Figure 4. Flow patterns for flow transition from pure diffusion/advection to full circulatory convection ($P=0.03$ atm, others are the same as in Figure 3).

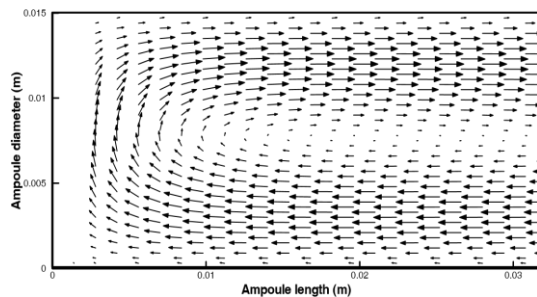


Figure 5. Flow patterns for full circulatory convection near the two ends. ($P=0.1$ atm, others are the same as in Figure 3).

6. Conclusion

Apart from costly and time consuming experimental research methods, in this paper, CFD modeling as a new research methodology in CVT processes is presented. Two dimensional simulations have been presented of the multicomponent transport phenomena and the multispecies, multi-reaction gas phase chemistry in

a CVT ampoule. A detailed description has been given of the problem definition and the model equations and parameters. Compared to the experimental literature values for all growth regimes, the modeling results agree with experimental ones qualitatively in TR values and accurately in the transition of TRs.

By using CFD modeling to investigate how several parameters influence the CVT ampoule, a greater understanding of the this process has been achieved. The new knowledge has been used to optimize the process design to give optimum conditions. Thus, this paper illustrates the potentials of CFD modeling to predict and optimize CVT process characteristics.

References

1. Endo H., Kuwana K., Saito K., Qian D., Andrews R., Grulke E.A. 2004. CFD prediction of carbon nanotube production rate in a CVD reactor, *Chemical Physics Letters* 387: 307–311.
2. Kleijn C. R. 2000. Transport Phenomena in Chemical Vapor Deposition Reactors, *Thin Solid Films* 365 (2000) 294-306.
3. Zuo R., Wang W. 2002. Theoretical Study on chemical vapor transport of ZnS-I₂ system. Part I. Kinetic process and one-dimensional model, *Journal of Crystal Growth* 236: 687–694.
4. Zuo R., Wang W. 2002. Theoretical study on chemical vapor transport of ZnS-I₂ system. Part II: numerical modeling, *Journal of Crystal Growth* 236: 695–710.
5. Ramachandran N., Su C.H., Lehoczy S.L. 2000. Modeling Studies of PVT Growth of ZnSe: Current Status and Future Course, *J. Crystal Growth* 208: 269-281.
6. Zhou H., Zebib A., Trivedi S., Duval W.M.B. 1996. Physical Vapor Transport of Zinc-Telluride by Dissociative Sublimation, *J. Crystal Growth* 167: 534-542.
7. Extremet G.P., Roux B., Bontoux P., Elie F. 1987. Two-dimensional Model for Thermal and Solutal Convection and Multi zone Physical Vapor Transport, *J. Crystal Growth* 82: 761-775.
8. Markham B.L., Rosenberger F. 1984. Diffusive-convective vapor transport across horizontal and inclined rectangular enclosures, *J. Crystal Growth* 67: 241-254.
9. Zappoli B., Mignon C., Launay J.C., Debegnac H. 1989. Germanium epitaxial growth in closed ampoules: II. Numerical modelling, *J. Crystal Growth* 94: 783 -794.
10. Patankar S.V. 1980. Numerical Heat Transfer and Fluid Flow, Hemisphere, Washington.
11. Dangel P.N., Wuensch B.J. 1973. Growth of Zinc Sulfide by Iodine Transport, *J. Crystal Growth* 19(1).